

Amendments to the Claims:

Claims 1-8 (Canceled).

9. (Previously Presented): An atomic layer deposition method of depositing an oxide on a substrate comprising:

providing a substrate within a deposition chamber;

chemisorbing a first species to form a first species monolayer onto the substrate within the deposition chamber from a gaseous precursor;

contacting the chemisorbed first species with remote plasma oxygen derived at least in part from at least one of O_2 and O_3 and with remote plasma nitrogen effective to react with the first species to form a monolayer comprising an oxide of a component of the first species monolayer; and

successively repeating the chemisorbing and the contacting with remote plasma oxygen and with remote plasma nitrogen effective to form porous electrically conductive oxide comprising $In_xSn_yO_z$ on the substrate, the gaseous precursor comprising an indium-containing precursor and a tin-containing precursor which are fed to the deposition chamber simultaneously.

10. (Previously Presented): An atomic layer deposition method of depositing an oxide on a substrate comprising:

providing a substrate within a deposition chamber;

chemisorbing a first species to form a first species monolayer onto the substrate within the deposition chamber from a gaseous precursor;

contacting the chemisorbed first species with remote plasma oxygen derived at least in part from at least one of O_2 and O_3 and with remote plasma nitrogen effective to react with the first species to form a monolayer comprising an oxide of a component of the first species monolayer; and

successively repeating the chemisorbing and the contacting with remote plasma oxygen and with remote plasma nitrogen effective to form porous electrically conductive oxide comprising In_xSn_yO . on the substrate, the gaseous precursor comprising an indium-containing precursor and a tin-containing precursor which are fed to the deposition chamber at different times.

11. (Original): The method of claim 10 wherein the different times overlap one another.

12. (Original): The method of claim 10 wherein the different times are spaced from one another.

Claims 13-34 (Canceled).

35. (Previously Presented): An atomic layer deposition method of depositing an oxide on a substrate comprising:

- providing a substrate within a deposition chamber;
- chemisorbing a first species to form a first species monolayer onto the substrate within the deposition chamber from a gaseous precursor;
- contacting the chemisorbed first species with remote plasma oxygen derived at least in part from at least one of O_2 and O_3 and with remote plasma nitrogen effective to react with the first species to form a monolayer comprising an oxide of a component of the first species monolayer, the remote plasma oxygen and the remote plasma nitrogen being fed separately to the deposition chamber simultaneously; and
- successively repeating the chemisorbing and the contacting with remote plasma oxygen and with remote plasma nitrogen effective to form porous oxide on the substrate.

Claim 36 (Canceled).

37. (Previously Presented): An atomic layer deposition method of depositing an oxide on a substrate comprising:

providing a substrate within a deposition chamber;

chemisorbing a first species to form a first species monolayer onto the substrate within the deposition chamber from a gaseous precursor;

contacting the chemisorbed first species with remote plasma oxygen derived at least in part from at least one of O_2 and O_3 and with remote plasma nitrogen effective to react with the first species to form a monolayer comprising an oxide of a component of the first species monolayer, the remote plasma oxygen and the remote plasma nitrogen are being generated in different remote plasma generating chambers; and

successively repeating the chemisorbing and the contacting with remote plasma oxygen and with remote plasma nitrogen effective to form porous oxide on the substrate.

38. (Original): The method of claim 37 wherein the remote plasma oxygen and the remote plasma nitrogen are fed as a mixture to the deposition chamber.

Claims 39-51 (Canceled).

52. (Previously Presented): An atomic layer deposition method of depositing an oxide on a substrate comprising:

providing a substrate within a deposition chamber;

chemisorbing a first species to form a first species monolayer onto the substrate within the deposition chamber from a gaseous precursor;

feeding a) at least one of O_2 and O_3 , and b) nitrogen to a remote plasma generator and forming a mixture of remote plasma oxygen and remote plasma nitrogen therefrom, the mixture comprising the remote plasma nitrogen at from 0.1% to 10% by volume of all remote plasma oxygen and remote plasma nitrogen generated by the generator;

feeding the remote plasma mixture to the deposition chamber and to contact the chemisorbed first species effective to react with the first species to form a monolayer comprising an oxide of a component of the first species monolayer; and

successively repeating the chemisorbing and the contacting with remote plasma oxygen and with remote plasma nitrogen effective to form porous oxide on the substrate, the gaseous precursor comprising an indium-containing precursor and a tin-containing precursor which are fed to the deposition chamber simultaneously.

53. (Previously Presented): An atomic layer deposition method of depositing an oxide on a substrate comprising:

providing a substrate within a deposition chamber;

chemisorbing a first species to form a first species monolayer onto the substrate within the deposition chamber from a gaseous precursor;

feeding a) at least one of O₂ and O₃, and b) nitrogen to a remote plasma generator and forming a mixture of remote plasma oxygen and remote plasma nitrogen therefrom, the mixture comprising the remote plasma nitrogen at from 0.1% to 10% by volume of all remote plasma oxygen and remote plasma nitrogen generated by the generator;

feeding the remote plasma mixture to the deposition chamber and to contact the chemisorbed first species effective to react with the first species to form a monolayer comprising an oxide of a component of the first species monolayer; and

successively repeating the chemisorbing and the contacting with remote plasma oxygen and with remote plasma nitrogen effective to form porous oxide on the substrate, the gaseous precursor comprising an indium-containing precursor and a tin-containing precursor which are fed to the deposition chamber at different times.

54. (Original): The method of claim 52 wherein the different times overlap one another.

55. (Original): The method of claim 52 wherein the different times are spaced from one another.

Claims 56-90 (Canceled).